

Notice of References Cited	Application/Control No. 10/589,680		Applicant(s)/Patent Under Reexamination NAKABAYASHI ET AL.	
	Examiner JONATHAN C. LANGMAN		Art Unit 1794	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,522,080	02-2003	Faillon et al.	315/169.3
*	B	US-6,218,680	04-2001	Carter et al.	257/77
*	C	US-5,119,540	06-1992	Kong et al.	118/730
*	D	US-2003/0233975	12-2003	Jenny et al.	117/30
*	E	US-2001/0023945	09-2001	Carter et al.	257/77
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Jenny et al. "Deep Level Transient spectroscopic and Hall Effect Investigation of the position of The Vanadium Acceptor Level in 4H and 6H-SiC", Applied Physics Letters, Vol. 68, Issue 14, April 1996, pgs 1963-1965.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.